

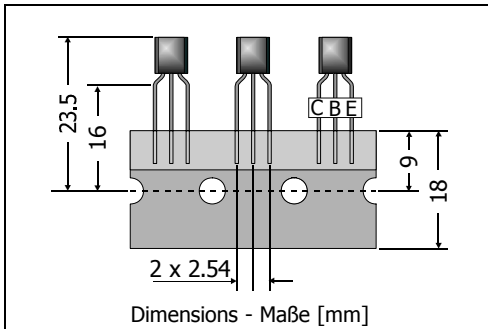
BC556 ... BC559

PNP

General Purpose Si-Epitaxial Planar Transistors
Si-Epitaxial Planar-Transistoren für universellen Einsatz

PNP

Version 2006-05-31



Power dissipation – Verlustleistung

500 mW

Plastic case
KunststoffgehäuseTO-92
(10D3)

Weight approx. – Gewicht ca.

0.18 g

Plastic material has UL classification 94V-0
Gehäusematerial UL94V-0 klassifiziertStandard packaging taped in ammo pack
Standard Lieferform gegurtet in Ammo-PackMaximum ratings ($T_A = 25^\circ\text{C}$)Grenzwerte ($T_A = 25^\circ\text{C}$)

			BC556	BC557	BC558/559
Collector-Emitter-voltage	E-B short	- V_{CES}	80 V	50 V	30 V
Collector-Emitter-voltage	B open	- V_{CEO}	65 V	45 V	30 V
Collector-Base-voltage	E open	- V_{CBO}	80 V	50 V	30 V
Emitter-Base-voltage	C open	- V_{EB0}	5 V		
Power dissipation – Verlustleistung		P_{tot}	500 mW ¹⁾		
Collector current – Kollektorstrom (dc)		- I_C	100 mA		
Peak Collector current – Kollektor-Spitzenstrom		- I_{CM}	200 mA		
Peak Base current – Basis-Spitzenstrom		- I_{BM}	200 mA		
Peak Emitter current – Emitter-Spitzenstrom		I_{EM}	200 mA		
Junction temperature – Sperrschichttemperatur		T_j	-55...+150°C		
Storage temperature – Lagerungstemperatur		T_s	-55...+150°C		

Characteristics ($T_j = 25^\circ\text{C}$)Kennwerte ($T_j = 25^\circ\text{C}$)

		Group A	Group B	Group C
DC current gain – Kollektor-Basis-Stromverhältnis ²⁾				
- $V_{CE} = 5\text{ V}$, - $I_C = 10\ \mu\text{A}$	h_{FE}	typ. 90	typ. 150	typ. 270
- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$	h_{FE}	110 ... 220	200 ... 450	420 ... 800
- $V_{CE} = 5\text{ V}$, - $I_C = 100\text{ mA}$	h_{FE}	typ. 120	typ. 200	typ. 400
h-Parameters at/bei - $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$				
Small signal current gain Kleinsignal-Stromverstärkung	h_{fe}	typ. 220	typ. 330	typ. 600
Input impedance – Eingangs-Impedanz	h_{ie}	1.6 ... 4.5 k Ω	3.2 ... 8.5 k Ω	6 ... 15 k Ω
Output admittance – Ausgangs-Leitwert	h_{oe}	18 < 30 μS	30 < 60 μS	60 < 110 μS
Reverse voltage transfer ratio Spannungsrückwirkung	h_{re}	typ. 1.5*10 ⁻⁴	typ. 2*10 ⁻⁴	typ. 3*10 ⁻⁴

1 Valid, if leads are kept at ambient temperature at a distance of 2 mm from case
Gültig wenn die Anschlussdrähte in 2 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden

Characteristics ($T_j = 25^\circ\text{C}$)Kennwerte ($T_j = 25^\circ\text{C}$)

	Min.	Typ.	Max.		
Collector-Emitter cutoff current – Kollektor-Emitter-Reststrom					
- $V_{CE} = 80\text{ V}$, (B-E short) BC546	- I_{CES}	–	0.2 nA	15 nA	
- $V_{CE} = 50\text{ V}$, (B-E short) BC547	- I_{CES}	–	0.2 nA	15 nA	
- $V_{CE} = 30\text{ V}$, (B-E short) BC548 / BC549	- I_{CES}	–	0.2 nA	15 nA	
- $V_{CE} = 80\text{ V}$, $T_j = 125^\circ\text{C}$, (B-E short) BC546	- I_{CES}	–	–	4 μA	
- $V_{CE} = 50\text{ V}$, $T_j = 125^\circ\text{C}$, (B-E short) BC547	- I_{CES}	–	–	4 μA	
- $V_{CE} = 30\text{ V}$, $T_j = 125^\circ\text{C}$, (B-E short) BC548 / BC549	- I_{CES}	–	–	4 μA	
Collector-Emitter saturation voltage – Kollektor-Emitter-Sättigungsspg²⁾					
- $I_C = 10\text{ mA}$, - $I_B = 0.5\text{ mA}$	- V_{CEsat}	–	80 mV	300 mV	
- $I_C = 100\text{ mA}$, - $I_B = 5\text{ mA}$	- V_{CEsat}	–	250 mV	650 mV	
Base-Emitter saturation voltage – Basis-Emitter-Sättigungsspannung²⁾					
- $I_C = 10\text{ mA}$, - $I_B = 0.5\text{ mA}$	- V_{BEsat}	–	700 mV	–	
- $I_C = 100\text{ mA}$, - $I_B = 5\text{ mA}$	- V_{BEsat}	–	900 mV	–	
Base-Emitter-voltage – Basis-Emitter-Spannung²⁾					
- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$	- V_{BE}	600 mV	660 mV	750 mV	
- $V_{CE} = 5\text{ V}$, - $I_C = 10\text{ mA}$	- V_{BE}	–	–	800 mV	
Gain-Bandwidth Product – Transitfrequenz					
- $V_{CE} = 5\text{ V}$, - $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	–	150 MHz	–	
Collector-Base Capacitance – Kollektor-Basis-Kapazität					
- $V_{CB} = 10\text{ V}$, $I_E = I_C = 0$, $f = 1\text{ MHz}$	C_{CBO}	–	3.5 pF	6 pF	
Emitter-Base Capacitance – Emitter-Basis-Kapazität					
- $V_{EB} = 0.5\text{ V}$, $I_C = I_E = 0$, $f = 1\text{ MHz}$	C_{EBO}	–	10 pF	–	
Noise figure – Rauschzahl					
- $V_{CE} = 5\text{ V}$, - $I_C = 200\text{ }\mu\text{A}$, $R_G = 2\text{ k}\Omega$ $f = 1\text{ kHz}$, $\Delta f = 200\text{ Hz}$	BC556 ... BC558 BC559	F F	– –	2 dB 1 dB	10 dB 4 dB
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft					
	R_{thA}	< 200 K/W ¹⁾			
Recommended complementary NPN transistors Empfohlene komplementäre NPN-Transistoren					
	BC546 ... BC549				
Available current gain groups per type Lieferbare Stromverstärkungsgruppen pro Typ					
	BC556A BC557A BC558A	BC556B BC557B BC558B BC559B	BC557C BC558C BC559C		

2 Tested with pulses $t_p = 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$ – Gemessen mit Impulsen $t_p = 300\text{ }\mu\text{s}$, Schaltverhältnis $\leq 2\%$

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